



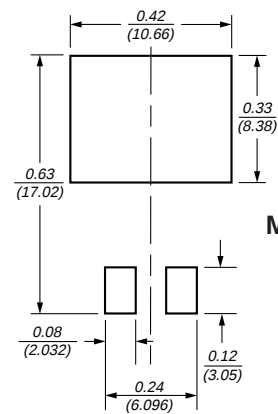
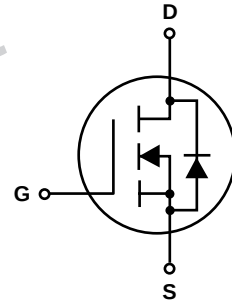
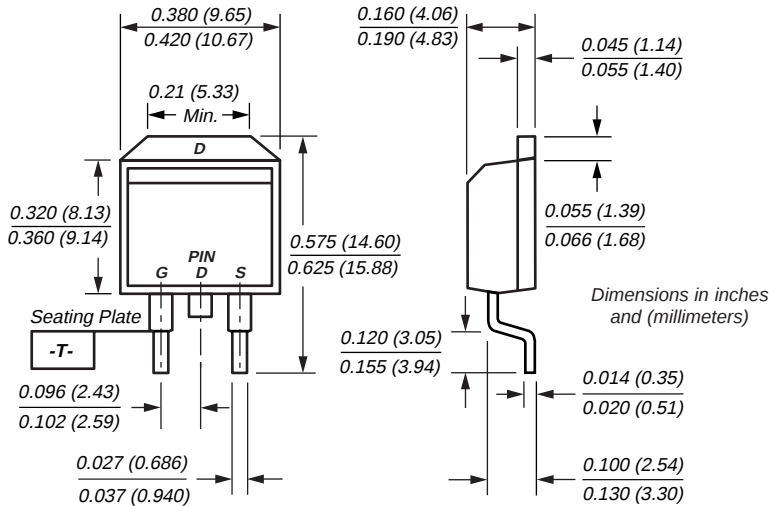
N-Channel Enhancement-Mode MOSFET

V_{DS} 55V $R_{DS(ON)}$ 20m Ω I_D 49A

**TRENCH
GENFET®**

New Product

TO-263AB



**Mounting Pad
Layout**

Mechanical Data

Case: JEDEC TO-263AB molded plastic body

Terminals: Leads solderable per MIL-STD-750, Method 2026

Mounting Position: Any **Weight:** 1.3g

Features

- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Specially Designed for Low Voltage DC/DC Converters
- Fast Switching for High Efficiency

Maximum Ratings and Thermal Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	55	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS} = 10\text{V}$	I_D	49 35	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	160	
Maximum Power Dissipation	P_D	94	W
Single Pulse Avalanche Energy ⁽²⁾	E_{AS}	210	mJ
Avalanche Current ⁽¹⁾	I_{AR}	25	A
Repetitive Avalanche Energy ⁽¹⁾	E_{AR}	11	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	1.6	$^\circ\text{C/W}$
Junction-to-Ambient Thermal Resistance ⁽³⁾	$R_{\theta JA}$	40	

Notes: (1) Repetitive rating; pulse width limited by max. junction temperature

(2) $V_{DD} = 25\text{V}$, starting $T_J = 25^\circ\text{C}$, $L = 470\mu\text{H}$, $R_G = 25\Omega$, $I_{AS} = 25\text{A}$

(3) Mounted on a 1 sq. inch, 2 oz. Cu pad on PCB.

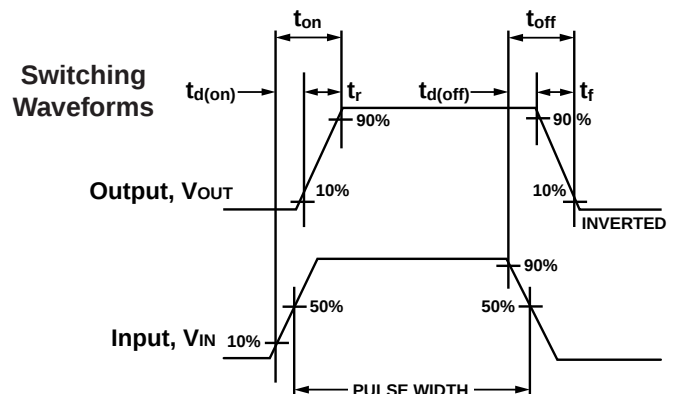
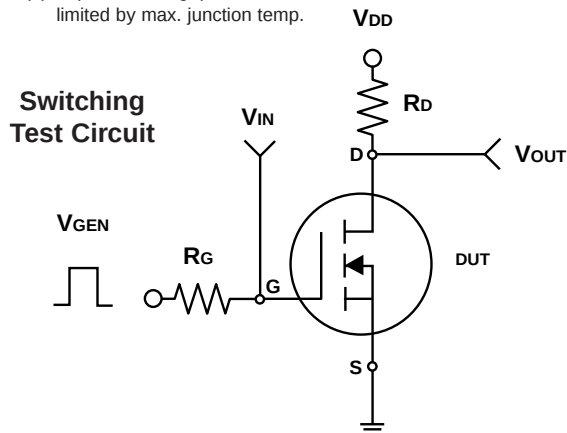
N-Channel Enhancement-Mode MOSFET

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	55	—	—	V
Drain-Source On-State Resistance ⁽¹⁾	R _{DS(on)}	V _{GS} = 10V, I _D = 25A	—	16	20	mΩ
		V _{GS} = 6V, I _D = 23A	—	18	22	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	—	4.0	V
Forward Transconductance ⁽¹⁾	g _{fs}	V _{DS} = 25V, I _D = 25A	17	78	—	S
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 55V, V _{GS} = 0V	—	—	25	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	—	—	±100	nA
Dynamic						
Total Gate Charge ⁽¹⁾	Q _g	V _{DS} = 44V, I _D = 25A, V _{GS} = 5V	—	29	40	nC
Gate-Source Charge ⁽¹⁾		V _{DS} = 44V, V _{GS} = 10V I _D = 25A	—	60	65	
Gate-Drain (“Miller”) Charge ⁽¹⁾	Q _{gd}		—	11	—	
Turn-On Delay Time ⁽¹⁾	t _{d(on)}	V _{DD} = 28V I _D = 25A, R _G = 12Ω R _D = 1.1Ω, V _{GEN} = 10V	—	13	—	ns
Rise Time ⁽¹⁾	t _r		—	19	34	
Turn-Off Delay Time ⁽¹⁾	t _{d(off)}		—	185	240	
Fall Time ⁽¹⁾	t _f		—	85	119	
Input Capacitance	C _{iss}	V _{GS} = 0V	—	3223	—	pF
Output Capacitance	C _{oss}	V _{DS} = 25V	—	308	—	
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz	—	135	—	
Source-Drain Diode						
Continuous Source Current	I _S	—	—	—	49	A
Pulsed Source Current ⁽²⁾	I _{SM}	—	—	—	160	
Diode Forward Voltage ⁽¹⁾	V _{SD}	I _S = 25A, V _{GS} = 0V	—	0.93	1.3	V
Source-Drain Reverse Recovery Time ⁽¹⁾	t _{rr}	I _F = 25A, di/dt = 100A/μs	—	53	—	ns
Source-Drain Reverse Recovery Charge ⁽¹⁾	Q _{rr}		—	93	—	nC

Notes: (1) Pulse width ≤ 300μs; duty cycle ≤ 2%

(2) Repetitive rating; pulse width limited by max. junction temp.



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Ratings and Characteristic Curves

Fig. 1 - Output Characteristics

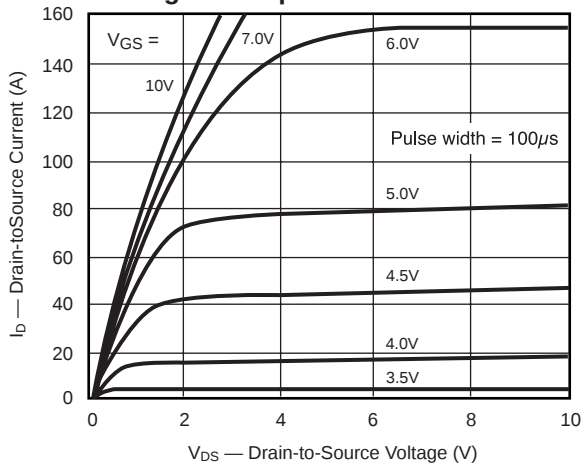
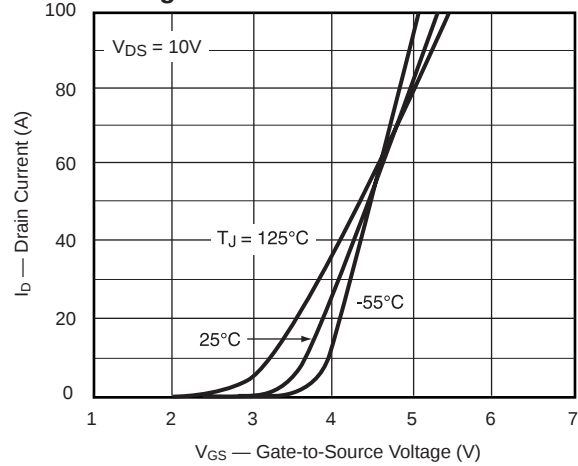


Fig. 2 - Transfer Characteristics



**Fig. 3 - On Resistance vs.
Drain Current**

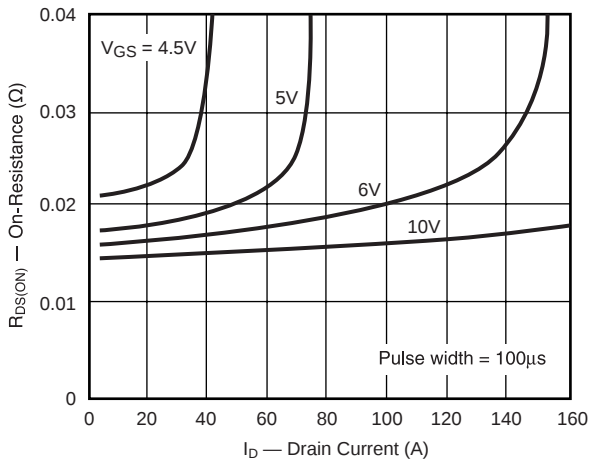


Fig. 4 - Capacitance

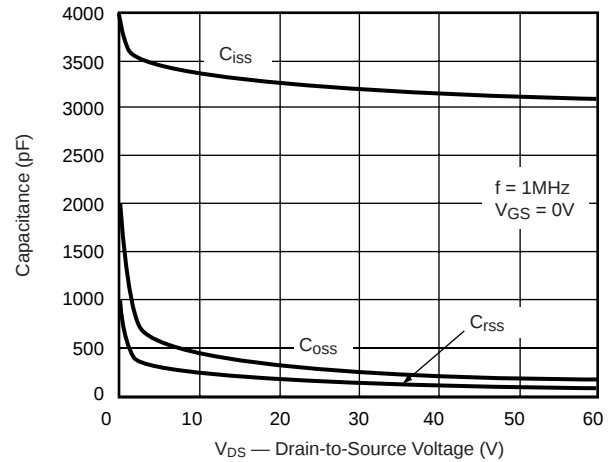
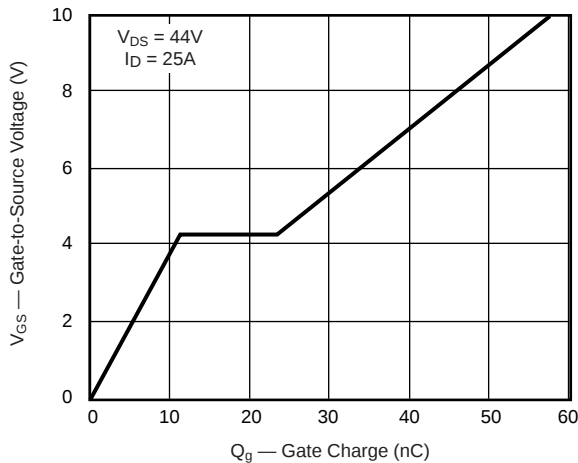


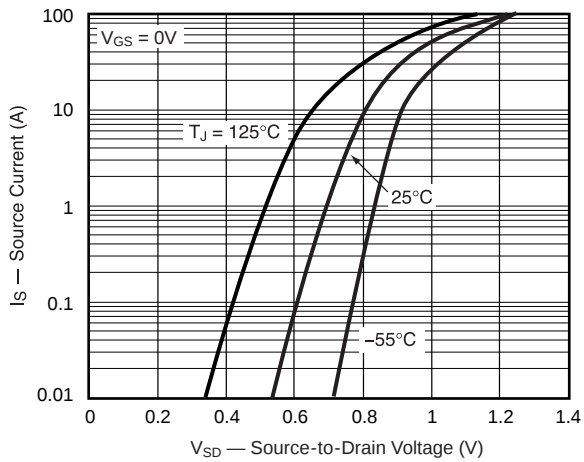
Fig. 5 - Gate Charge



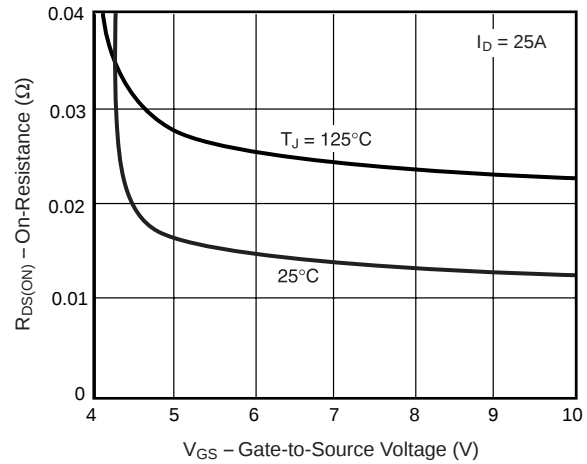
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Ratings and Characteristic Curves

**Fig. 6 - Source-Drain Diode
Forward Voltage**



**Fig. 7 - On-Resistance
vs. Gate-to-Source Voltage**



**Fig. 8 - Breakdown Voltage vs.
Junction Temperature**

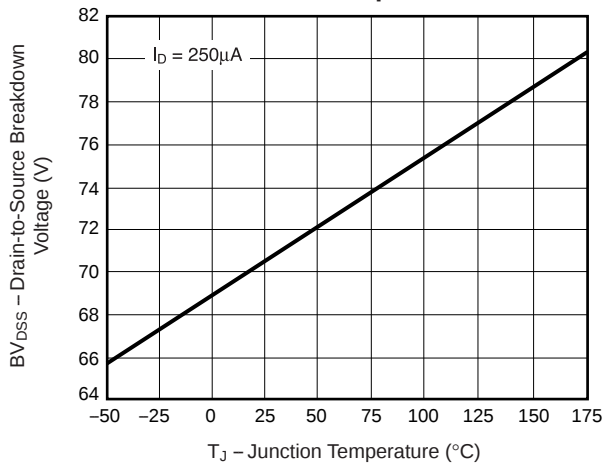
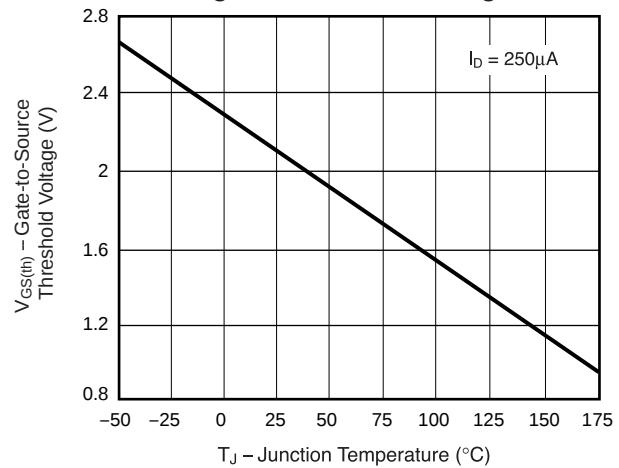


Fig. 9 - Threshold Voltage



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Ratings and Characteristic Curves

Fig. 10 – On-Resistance vs. Junction Temperature

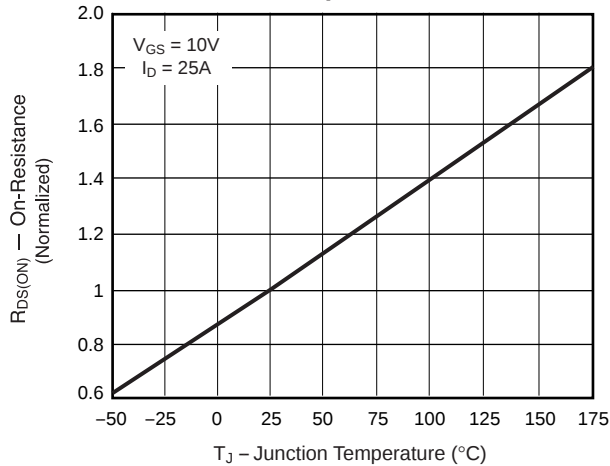


Fig. 11 – Thermal Impedance

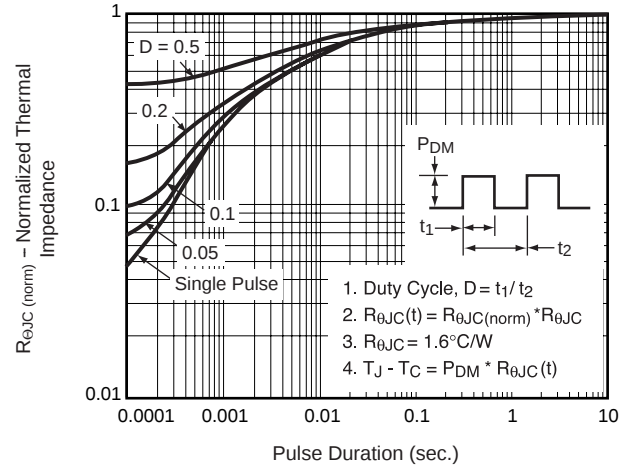


Fig. 12 – Power vs. Pulse Duration

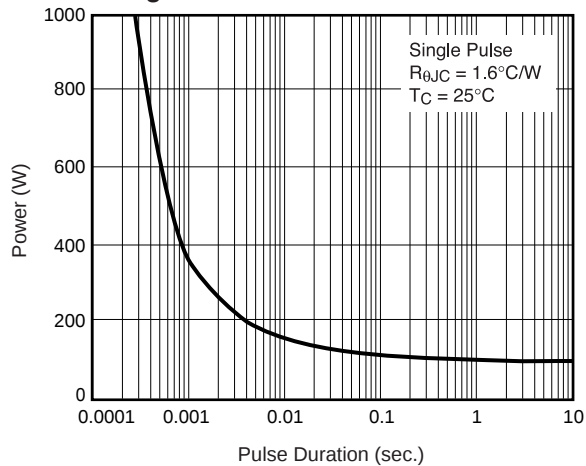


Fig. 13 – Maximum Safe Operating Area

